

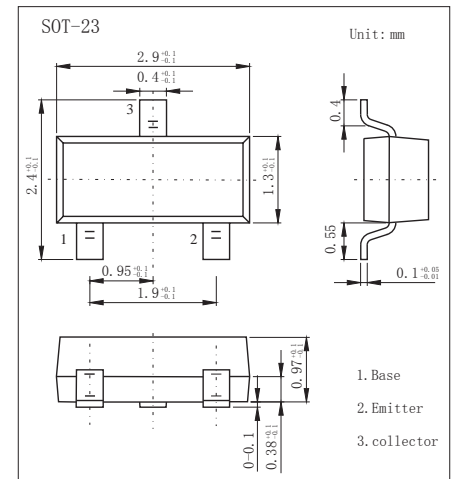
## SOT-23 Plastic-Encapsulate Transistors

### FEATURES

- TRANSISTOR (PNP)
- Complement to KSC2859

### MECHANICAL DATA

- Case style:SOT-23molded plastic
- Mounting position:any



### MAXIMUM RATINGS AND CHARACTERISTICS

@ 25°C Ambient Temperature (unless otherwise noted)

Symbol	Parameter	Value	Unit
$V_{CB0}$	Collector-Base Voltage	-35	V
$V_{CEO}$	Collector-Emitter Voltage	-30	V
$V_{EBO}$	Emitter-Base Voltage	-5	V
$I_C$	Collector Current -Continuous	-0.5	A
$P_C$	Collector Power Dissipation	150	mW
$T_j$	Junction Temperature	150	°C
$T_{stg}$	Storage Temperature	-55-150	°C

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=-100\mu A, I_E=0$	-35			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=-1mA, I_B=0$	-30			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=-100\mu A, I_C=0$	-5			V
Collector cut-off current	$I_{CBO}$	$V_{CB}=-35V, I_E=0$			-0.1	$\mu A$
Emitter cut-off current	$I_{EBO}$	$V_{EB}=-5V, I_C=0$			-0.1	$\mu A$
DC current gain	$h_{FE(1)}$	$V_{CE}=-1V, I_C=-100mA$	70		240	
	$h_{FE(2)}$	$V_{CE}=-6V, I_C=-400mA$	25			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=-100mA, I_B=-10mA$			-0.25	V
Base-emitter voltage	$V_{BE}$	$V_{CE}=-1V, I_C=-100mA$			-1.0	V
Transition frequency	$f_T$	$V_{CE}=-6V, I_C=-20mA$		200		MHz
Collector output capacitance	$C_{ob}$	$V_{CB}=-6V, I_E=0, f=1MHz$		13		pF

### CLASSIFICATION OF $h_{FE(1)}$

Rank	O	Y
Range	70-140	120-240
Marking	F10	F1Y